

Kadir Ejderha

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/901507/publications.pdf>

Version: 2024-02-01

25
papers

525
citations

687363

13
h-index

642732

23
g-index

25
all docs

25
docs citations

25
times ranked

459
citing authors

#	ARTICLE	IF	CITATIONS
1	Capacitance-conductance-current-voltage characteristics of atomic layer deposited Au/Ti/Al ₂ O ₃ /n-GaAs MIS structures. <i>Materials Science in Semiconductor Processing</i> , 2015, 39, 400-407.	4.0	108
2	On temperature-dependent experimental I-V and C-V data of Ni/n-GaN Schottky contacts. <i>Journal of Applied Physics</i> , 2010, 108, .	2.5	104
3	Examination by interfacial layer and inhomogeneous barrier height model of temperature-dependent I-V characteristics in Co/p-InP contacts. <i>Journal of Alloys and Compounds</i> , 2009, 484, 870-876.	5.5	34
4	Dependence of characteristic diode parameters on sample temperature in Ni/epitaxy n-Si contacts. <i>Materials Science in Semiconductor Processing</i> , 2011, 14, 5-12.	4.0	32
5	Influence of interface states on the temperature dependence and current-voltage characteristics of Ni/p-InP Schottky diodes. <i>Superlattices and Microstructures</i> , 2010, 47, 241-252.	3.1	29
6	The electrical characterizations and illumination response of Co/N-type GaP junction device. <i>Current Applied Physics</i> , 2015, 15, 1054-1061.	2.4	24
7	The Characteristic Parameters of Ni/n-6H-SiC Devices Over a Wide Measurement Temperature Range. <i>Silicon</i> , 2017, 9, 395-401.	3.3	19
8	Effect of temperature on the current (capacitance and conductance)-voltage characteristics of Ti/n-GaAs diode. <i>Journal of Applied Physics</i> , 2014, 116, .	2.5	18
9	The effect of annealing temperature on the electrical characterization of Co/n type GaP Schottky diode. <i>Materials Research Bulletin</i> , 2015, 61, 463-468.	5.2	17
10	Determination of contact parameters of Ni/n-GaP Schottky contacts. <i>Microelectronics Reliability</i> , 2012, 52, 1005-1011.	1.7	16
11	Temperature dependence of electrical parameters of the Cu/n-Si metal semiconductor Schottky structures. <i>Journal of Molecular Structure</i> , 2021, 1224, 129057.	3.6	16
12	Schottky barrier height modification in Au/n-type 6H-SiC structures by PbS interfacial layer. <i>Microelectronic Engineering</i> , 2011, 88, 179-182.	2.4	15
13	Electrical and optical characteristics of Au/PbS/n-6H-SiC structures prepared by electrodeposition of PbS thin film on n-type 6H-SiC substrate. <i>Journal of Alloys and Compounds</i> , 2011, 509, 3155-3159.	5.5	14
14	The Effect of Thermal Annealing and Measurement Temperature on Interface State Density Distribution and Time Constant in Ni/n-GaP Rectifying Contacts. <i>Journal of Electronic Materials</i> , 2018, 47, 3502-3509.	2.2	14
15	Responses of Pt/n-InP Schottky diode to electron irradiation in different temperature conditions. <i>Journal of Radioanalytical and Nuclear Chemistry</i> , 2011, 289, 145-148.	1.5	10
16	Characterization of CuO/n-Si heterojunction solar cells produced by thermal evaporation. <i>Materials Science-Poland</i> , 2018, 36, 668-674.	1.0	10
17	Dependence of Electrical Properties of Ni/n-GaP/Al Schottky Contacts on Measurement Temperature and Thermal Annealing. <i>Journal of Electronic Materials</i> , 2021, 50, 6741-6747.	2.2	9
18	Temperature-dependent current-voltage characteristics in thermally annealed ferromagnetic Co/n-GaN Schottky contacts. <i>EPJ Applied Physics</i> , 2014, 68, 20101.	0.7	8

#	ARTICLE	IF	CITATIONS
19	Characteristic diode parameters in thermally annealed Ni/p-InP contacts. Journal of Semiconductors, 2016, 37, 044001.	3.7	7
20	Temperature dependence of interface state density distribution determined from conductanceâ€“frequency measurements in Ni/n-GaP/Al diode. Journal of Materials Science: Materials in Electronics, 2020, 31, 21260-21271.	2.2	7
21	Temperature-dependent I-V characteristics in thermally annealed Co/p-InP contacts. EPJ Applied Physics, 2012, 57, 10102.	0.7	6
22	THE CHARACTERISTIC DIODE PARAMETERS IN Ti/p-InP CONTACTS PREPARED BY DC SPUTTERING AND EVAPORATION PROCESSES OVER A WIDE MEASUREMENT TEMPERATURE. Surface Review and Letters, 2017, 24, 1750052.	1.1	6
23	Effect of different sound atmospheres on SnO ₂ :Sb thin films prepared by dip coating technique. Modern Physics Letters B, 2017, 31, 1750288.	1.9	1
24	Analysis and Comparison of the Main Electrical Characteristics of Cu/n-type Si metal semiconductor structures at wide temperature Range. Silicon, 2022, 14, 3493-3500.	3.3	1
25	Temperature dependence of interface-state density distributions in Cu/CuO/n-type Si structures. Materials Today: Proceedings, 2021, 46, 7030-7032.	1.8	0